

TT2190

/ Absolute Maximum Ratings(Ta=25)

	℃		
			℃
			℃

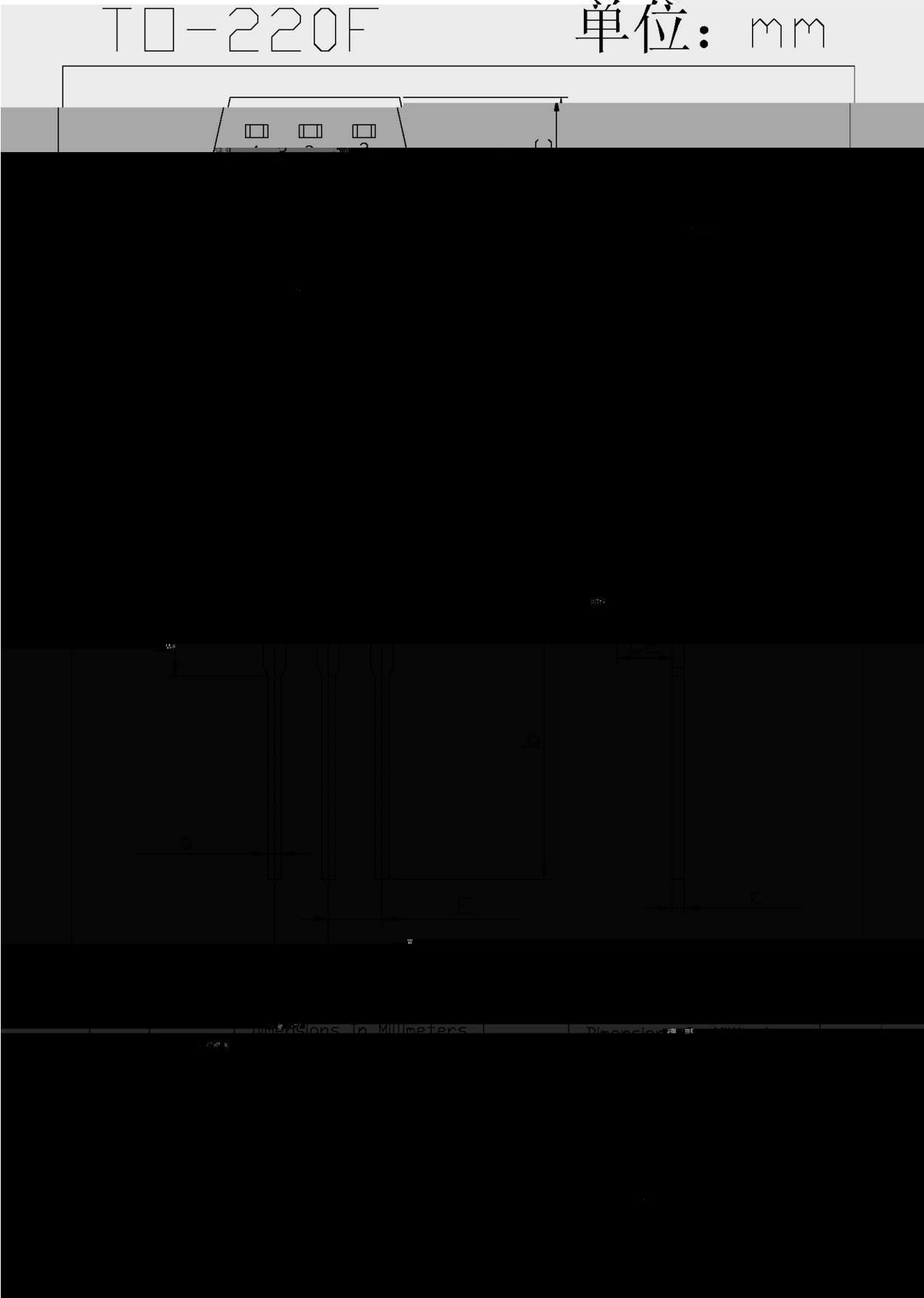
/ Electrical Characteristics(Ta=25)

						μ
						μ

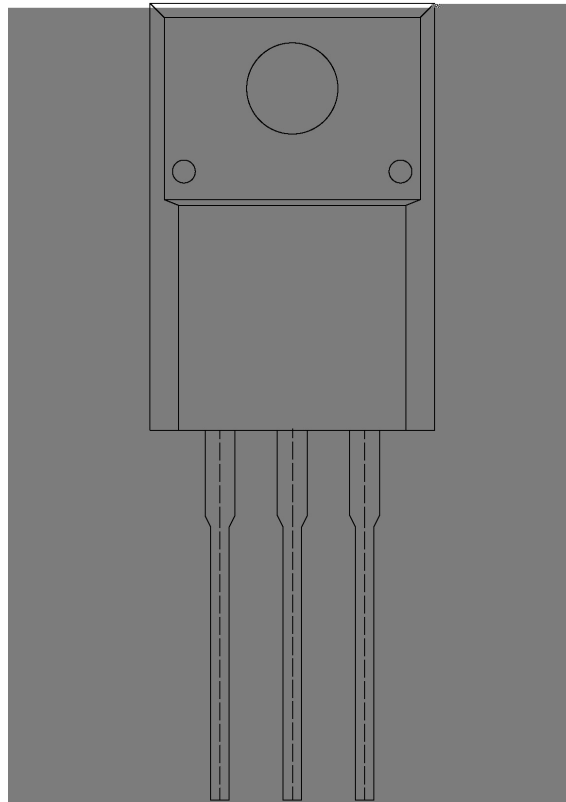
The figure displays several characteristic curves for the 2N4350 PNP silicon NPN transistor:

- IC - V_{BE} and IC - V_{CE}:** Graphs showing collector current (I_C) versus base-emitter voltage (V_{BE}) and collector-emitter voltage (V_{CE}). The V_{CE} is 5V.
- h_{FE} - I_C:** Graph showing the DC current gain (h_{FE}) versus collector current (I_C). The V_{CE} is 5V.
- V_{CE(sat)} - I_C:** Graph showing the collector-emitter saturation voltage (V_{CE(sat)}) versus collector current (I_C). The V_{BE} is 1.0V.
- PC - T_a and PC - T_c:** Graphs showing the power dissipation (P_C) versus ambient temperature (T_a) and case temperature (T_c). The T_c is 120°C.

/ Package Dimensions



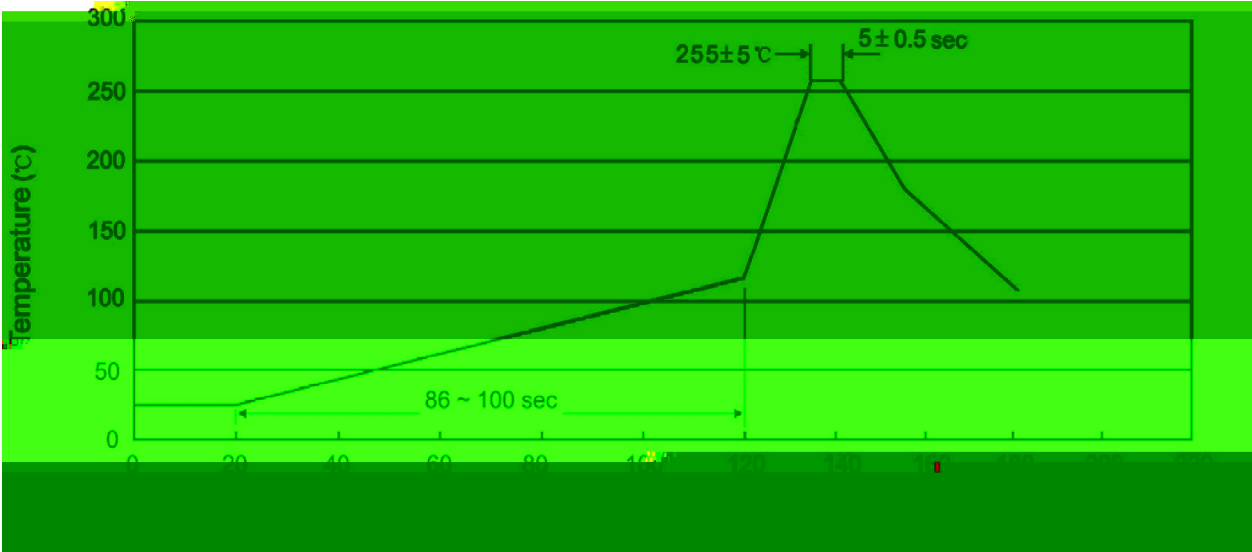
/ Marking Instructions



BR

TT2190

() / Temperature Profile for Dip Soldering(Pb-Free)



± ± ± ±

/ Resistance to Soldering Heat Test Conditions

± ± °C

/ Packaging SPEC.

/ Notices